

BSS64LT1G

Driver Transistor

NPN Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	80	Vdc
Collector – Base Voltage	V_{CBO}	120	Vdc
Emitter – Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

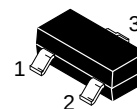
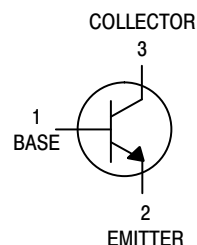
1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



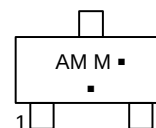
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SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



AM = Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BSS64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSS64LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

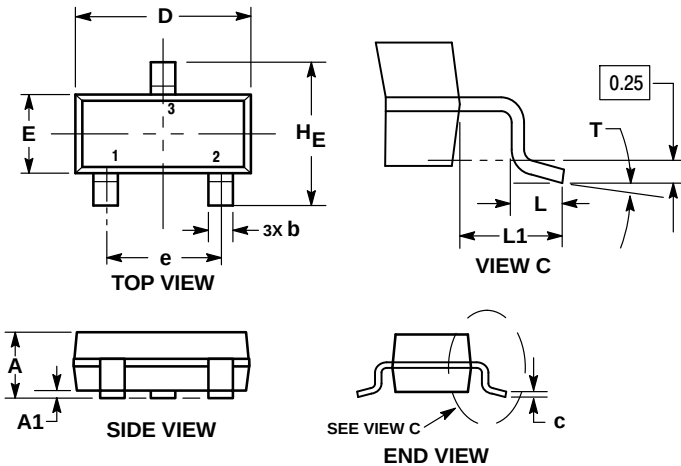
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (I _C = 4.0 mA _{dc})	V _{(BR)CEO}	80	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 100 µA _{dc})	V _{(BR)CBO}	120	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 100 µA _{dc})	V _{(BR)EBO}	5.0	–	V _{dc}
Collector Cutoff Current (V _{CE} = 90 V _{dc}) (T _A = 150°C)	I _{CBO}	– –	0.1 500	µA _{dc}
Emitter Cutoff Current (V _{EB} = 4.0 V _{dc})	I _{EBO}	–	200	nA _{dc}
ON CHARACTERISTICS				
DC Current Gain (V _{CE} = 1.0 V _{dc} , I _C = 10 mA _{dc})	H _{FE}	20	–	–
Collector–Emitter Saturation Voltage (I _C = 4.0 mA _{dc} , I _B = 400 µA _{dc}) (I _C = 50 mA _{dc} , I _B = 15 mA _{dc})	V _{CE(sat)}	– –	0.15 0.2	V _{dc}
Forward Base–Emitter Voltage	V _{BE(sat)}	–	–	–
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (I _C = 4.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 20 MHz)	f _T	60	–	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , f = 1.0 MHz)	C _{ob}	–	20	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BSS64LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AR



NOTES:

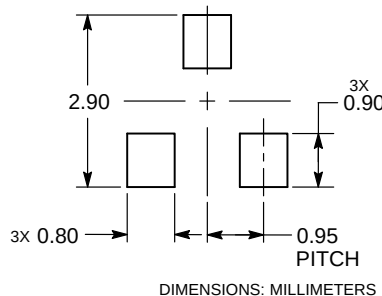
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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